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RFMD Wins DARPA GaN Contract to Enhance High Power RF Amplifier Performance

GREENSBORO, N.C., Oct. 25, 2012 (GLOBE NEWSWIRE) -- RF Micro Devices, Inc. (Nasdaq:RFMD), a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies, today announced it has been awarded a \$2.1 million contract from the Defense Advanced Research Projects Agency (DARPA) to enhance the thermal efficiency of gallium nitride (GaN) circuits used in high power radar and other military systems.

The award is in association with the Near Junction Thermal Transport (NJTT) effort of DARPA's Thermal Management Technologies (TMT) program. The goal of the DARPA NJTT initiative is to achieve a 3x or greater improvement in power handling from GaN power amplifiers through improved thermal management of the near junction region. By combining thermally-enhanced diamond substrates with RFMD's industry-leading GaN-on-SiC high power technology, RFMD expects to significantly improve power density and power handling capability.

Jeff Shealy, vice president and general manager of RFMD's Power Broadband business unit, said, "RFMD is excited to work with DARPA to apply new technologies to our existing portfolio of GaN-based high power RF amplifier products. We expect the NJTT program will result in a new generation of higher performing, more compact RF high power amplifiers (HPAs) with lower operating temperature and greater RF power-per-unit area."

RFMD's partners in the program include the Georgia Institute of Technology, Stanford University, Group4 Labs, and Boeing. Georgia Tech is recognized for its leadership in thermal testing, modeling and micro Raman thermography. Stanford University is the world leader in thermal measurement of the critical interface layers within a transistor die. Group4 Labs is a pioneer in the development of diamond substrates. Finally, Boeing plans to evaluate the resulting technology to assess its projected impact on future defense systems.

RFMD has been a leader in GaN technology since 2000 and has production released two high power process technologies available through its open-foundry business model. RFMD's GaN power devices have been deployed across multiple defense and commercial applications, including radar, milcom, and CATV infrastructure. RFMD is the world leader in GaN-based CATV broadband amplifiers with superior linearity and output power and has shipped over 350,000 GaN-based CATV amplifiers into the commercial market.

About RFMD

RF Micro Devices, Inc. (Nasdaq:RFMD) is a global leader in the design and manufacture of high-performance radio frequency components and compound semiconductor technologies. RFMD's products enable worldwide mobility, provide enhanced connectivity and support advanced functionality in the mobile device, wireless infrastructure, wireless local area network (WLAN or WiFi), cable television (CATV)/broadband, Smart Energy/advanced metering infrastructure (AMI), and aerospace and defense markets. RFMD is recognized for its diverse portfolio of semiconductor technologies and RF systems expertise and is a preferred supplier to the world's leading mobile device, customer premises and communications equipment providers.

Headquartered in Greensboro, N.C., RFMD is an ISO 9001-, ISO 14001-, and ISO/TS 16949-certified manufacturer with worldwide engineering, design, sales and service facilities. RFMD is traded on the NASDAQ Global Select Market under the symbol RFMD. For more information, please visit RFMD's web site at www.rfmd.com.

The RF Micro Devices, Inc. logo is available at <http://www.globenewswire.com/newsroom/prs/?pkgid=6436>

This press release includes "forward-looking statements" within the meaning of the safe harbor provisions of the Private Securities Litigation Reform Act of 1995. These forward-looking statements include, but are not limited to, statements about our plans, objectives, representations and contentions and are not historical facts and typically are identified by use of terms such as "may," "will," "should," "could," "expect," "plan," "anticipate," "believe," "estimate," "predict," "potential," "continue" and similar words, although some forward-looking statements are expressed differently. You should be aware that the forward-looking statements included herein represent management's current judgment and expectations, but our actual results, events and performance could differ materially from those expressed or implied by forward-looking statements. We do not intend to update any of these forward-looking statements or publicly announce the results of any revisions to these forward-looking statements, other than as is required under the federal securities laws. RF Micro Devices' business is subject to numerous risks and uncertainties, including variability in operating results, risks associated with the impact of global macroeconomic and credit conditions on our business and the business of our suppliers and customers, our reliance on a few large customers for a

substantial portion of our revenue, the rate of growth and development of wireless markets, our ability to bring new products to market, our reliance on inclusion in third party reference designs for a portion of our revenue, our ability to manage channel partner and customer relationships, risks associated with the operation of our wafer fabrication, molecular beam epitaxy, assembly and test and tape and reel facilities, our ability to complete acquisitions and integrate acquired companies, including the risk that we may not realize expected synergies from our business combinations, our ability to attract and retain skilled personnel and develop leaders, variability in production yields, raw material costs and availability, our ability to reduce costs and improve margins in response to declining average selling prices, our ability to adjust production capacity in a timely fashion in response to changes in demand for our products, dependence on gallium arsenide (GaAs) for the majority of our products, dependence on third parties, and substantial reliance on international sales and operations. These and other risks and uncertainties, which are described in more detail in RF Micro Devices' most recent Annual Report on Form 10-K and other reports and statements filed with the Securities and Exchange Commission, could cause actual results and developments to be materially different from those expressed or implied by any of these forward-looking statements.

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